Patent and Trad

PTO/SB/08A or use through 10/31/2002. OMB 0651-0031 Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act

.35, no persons are required to respond to a collection of informa..... unless it contains a valid OMB control number

C mplete if Kn wn Substitute for form 1449A/PTO **Application Number** TBA INFORMATION DISCLOSURE Herewith **Filing Date** STATEMENT BY APPLICANT First Named Invent r Christopher B. Kocon **Group Art Unit** (use as many sheets as nec ssary) **Examiner Name** E. Ortiz (Recommended) Attorney Docket Number 90065.146801 Sheet of

	Cite No.1	U.S. Patent Document		Name of Datastas or Applicant	Date of Publication of	Pages, Columns, Lines, Where Relevant
Examiner Initials		Number	Kind Code ² (if known)	Name of Patentee or Applicant of Cited Document	Cited Document MM-DD-YYYY	Passages or Relevant Figures Appear
TET	*1	4,969,028		Baliga	11/06/1990	
468	*2	4,364,073		Becke, et al.	12/14/1982	
38	¥3	5,986,304		Hshieh, et al.	11/16/1999	· · · ·
354	*4	5,877,520		Hynecek	03/02/1991	
Car	*5	5,929,481		Hshieh, et al.	07/27/1999	
KAP	*6	5,998,836		Williams	12/07/1999	
76	* 7	5,998,837		Williams	12/07/1999	
1860	*8	5,828,100		Tamba, et al.	10/27/1998	
730	* 9	5,864,159		Takahashi	01/26/1999	
481	*10	6,043,531		Stecher, et al.	03/28/2000	
430	*11	5,907,169		Hshieh, et al.	05/25/1999	
1861	*12	5,977,588		Patel	11/02/1999	
						·
					لمصا	
					111-	· · · · · · · · · · · · · · · · · · ·

		·····				

Examiner Initials*			Foreign Patent Do	cument	Name of Patentee or	Date of Publication of	Pages, Columns, Lines, Where Relevant	1
	Cite No. ¹	Office ³	Number ⁴	Kind Code ⁵ (if known)	Applicant of Cited Document	Cited Document MM-DD-YYYY	Passages or Relevant Figures Appear	Te
TAN	*13	JP	02144971		Hitachi, Ltd.	04/06/1990		
400	*14	EP	00102398.5		European Patent Office	09/22/2000		\perp
1	*15	JP	11354780		Nissan Motor Co. Ltd.	12/24/1999		
1	*16	JP	4,05-275691		Okabe	10/1993		┷
654	*17	JP	405-82791		Maruyama	04/1993		\perp
382	*18	JP	405-347414		Terajima	10/1993		+
					120			土
				7				

Date Examiner Considered Signature

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). 4 For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. 5 Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁸ Applicant is to place a check mark here if English language Translation is attached.

Signature

PTO/SB/08B (08-00)
Patent and Trat
Office: U.S. DEPARTMENT OF COMMERCE
a collection of informatic unless it contains a valid OMB control number.

Substitute for form 1449B/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(us as many sheets as necessary)

Shoot	2	of	2
Sheet	2	וטן	

·		_
C	mpl te if Kn wn	
Application Number	ТВА	
Filing Date	Herewith	
First Named Inventor	Christopher B. Kocon	
Group Art Unit	2815	
Examiner Name	E. Ortiz (Recommended)	
Attorney Docket Number	90065.146801	J

Examiner	Cite	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s),	T2
Initials*	No.1	publisher, city and/or country where published.	_
36	19	Jonathan Evans, et al, "The Behaviour of Very High Current Density Power MOSFET's", IEEE Electron Devices Society, pp. 157-160 (May 1996).	
		Jonathan Evans, et al., "The Behavior of Very High Current Density Power MOSFET's, <u>IEEE Transactions on Electron Devices</u> , Vol. 44. No. 7, pp. 1148-1153 (July 1997).	
2/1	2 21	Bulucea, Constantin, et al., "Trench DMOS Transistor Technology for High-Current (100 A Range) Switching", Solid-State Electronics, Vol. 34, Vol. 5, Head Hill Hall, Oxford, GB, pp. 493-507 (May 1991).	
199	31	Matsumoto, Satoshi, et al., "A High Performance Self-Aligned UMOSFET With a Vertical Trench Contact Structure", IEEE Transactions on Electron Devices, Vol. 41, No. 5, New York, New York, US, pp. 1-5 (May 1994).	
4	23	International Search Report	
	*	The above listed patents weere cried in the parent application.	
		La	
<u> </u>	+		+
			"
	<u> </u>		

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Considered

¹ Unique citation designation number. ² Applicant is to place a check mark here if English language Translation is attached.